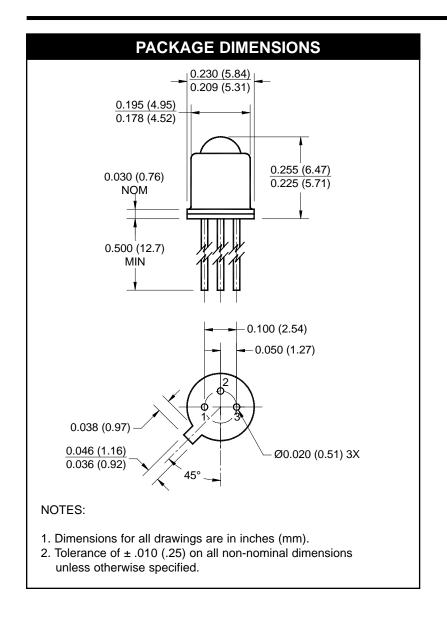
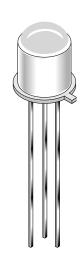
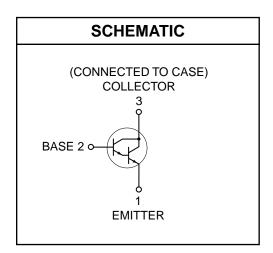


L14F1 L14F2







DESCRIPTION

The L14F1/L14F2 are silicon photodarlingtons mounted in a narrow angle, TO-18 package.

FEATURES

- Hermetically sealed package
- Narrow reception angle



HERMETIC SILICON PHOTODARLINGTON

L14F1 L14F2

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise specified)								
Parameter	Symbol	Rating	Unit					
Operating Temperature	T _{OPR}	-65 to +125	°C					
Storage Temperature	T _{STG}	-65 to +150	°C					
Soldering Temperature (Iron)(3,4,5 and 6)	T _{SOL-I}	240 for 5 sec	°C					
Soldering Temperature (Flow)(3,4 and 6)	T _{SOL-F}	260 for 10 sec	°C					
Collector to Emitter Breakdown Voltage	V _{CEO}	25	V					
Collector to Base Breakdown Voltage	V _{CBO}	25	V					
Emitter to Base Breakdwon Voltage	V _{EBO}	12	V					
Power Dissipation (T _A = 25°C) ⁽¹⁾	P _D	300	mW					
Power Dissipation (T _C = 25°C) ⁽²⁾	P _D	600	mW					

NOTE:

- 1. Derate power dissipation linearly 3.00 mW/°C above 25°C ambient.
- 2. Derate power dissipation linearly 6.00 mW/°C above 25°C case.
- 3. RMA flux is recommended.
- 4. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 5. Soldering iron tip 1/16" (1.6mm) minimum from housing.
- 6. As long as leads are not under any stress or spring tension.
- 7. Light source is a GaAs LED emitting light at a peak wavelength of 940 nm.
- 8. Figure 1 and figure 2 use light source of tungsten lamp at 2870°K color temperature. A GaAs source of 0.05 mW/cm² is approximately equivalent to a tungsten source, at 2870°K, of 0.2 mW/cm².

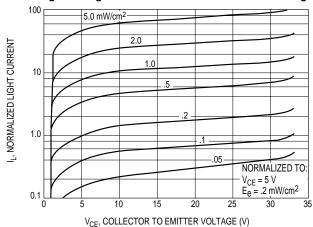
ELECTRICAL / OPTICAL CHARACTERISTICS (TA =25°C) (All measurements made under pulse conditions)								
PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS		
Collector-Emitter Breakdown	$I_{C} = 10 \text{ mA}, Ee = 0$	BV _{CEO}	25		_	V		
Emitter-Base Breakdown	I _E = 100 μA, Ee = 0	BV _{EBO}	12		_	V		
Collector-Base Breakdown	I _C = 100 μA, Ee = 0	BV _{CBO}	25		_	V		
Collector-Emitter Leakage	V _{CE} = 12 V, Ee = 0	I _{CEO}	_		100	nA		
Reception Angle at 1/2 Sensitivity		θ		±8		Degrees		
On-State Collector Current L14F1	Ee = .125 mW/cm ² , $V_{CE} = 5 V^{(7)}$	I _{C(ON)}	7.5		_	mA		
On-State Collector Current L14F2	Ee = .125 mW/cm ² , $V_{CE} = 5 V^{(7)}$	I _{C(ON)}	2.5			mA		
Rise Time	$I_{C} = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_{L} = 100 \Omega$	t _r		300		μs		
Fall Time	I_C = 10 mA, V_{CC} = 5 V, R_L =100 Ω	t _f		250		μs		



HERMETIC SILICON PHOTODARLINGTON

L14F1 L14F2

Figure 1. Light Current vs. Collector to Emitter Voltage



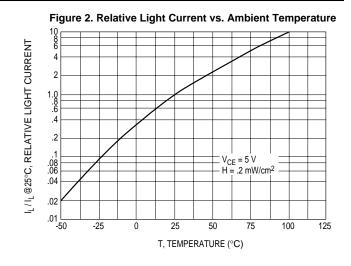
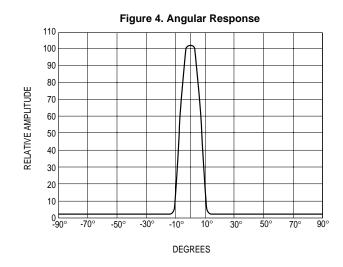


Figure 3. Spectral Response 1.0 0.9 RELATIVE SPECTRAL RESPONSE 0.8 0.7 0.6 0.4 0.3 0.1 0 400 500 600 700 800 900 1000 1100

 λ , WAVE LENGTH (NANOMETERS)



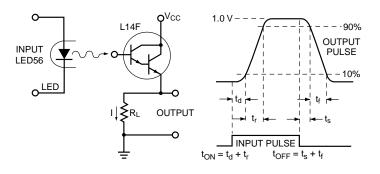
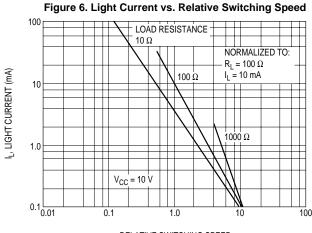


Figure 5. Test Circuit and Voltage Waveforms



RELATIVE SWITCHING SPEED td + tr + ts + tf



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- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.